# Cooled Photodiode Si APD 0.4 – 1.1 µm





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The CSAD serials cooled Silicon APD photodiode provides high sensitivity with gain for detecting from UV to near-infrared light in the 0.4-1.1  $\mu$ m range. These detectors are hermetically sealed to ensure longevity. Within the detector package, a thermoelectric cooler is integrated with a 3-stage deep cooling as well as integration with a MEMS chopper, significantly reducing background noise while maintaining a compact format. A thermistor is also included in the package to sense the Si photodiode chip temperature for stable operation. It is designed for low-light-level detection applications. Additionally, we offer driving PCB consists a precision TEC temperature controller, an amplifier, and a detector heat sink for convenient use.

#### **Features**

- 0.4 1.1 µm
- Low Noise
- High Sensitivity
- Hermetic Sealed Detector
- MEMS Chopper Integration Option

### **Applications**

- OEM
- Lab user
- Instruments

#### **Specifications**

Parameter	Min	Typical	Max	Unit
Central Wavelength	400	960	1100	nm
Sensor Active Diameter	0.25		0.3	mm
Responsivity (@960nm, 1 μW, 100gain)	50	55		A/W
Dark Current (@0.1V, -40 °C)	0.2		0.5	nA
Gain		100		
Breakdown Voltage	160		200	V
Cut Off Frequency (@1V)	80		20	MHz
Capacitance (@0V, 100gain)		0.5		pF
Temperature Coefficient		1.1		V/°C
Operating Temperature	-40		75	°C
Storage Temperature	-50		85	°C
TEC Cooler Power		<2.1V@2A		W

**Note:** The specifications provided are for general applications with a cost-effective approach. If you need to narrow or expand the tolerance, coverage, limit, or qualifications, please [click this <u>link</u>]:

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Rev 11/03/25







# **Cooled Photodiode Si APD**

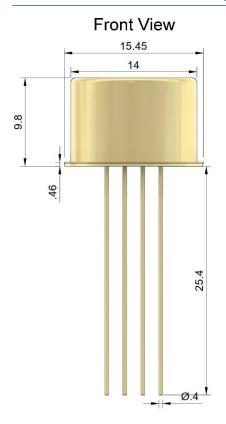


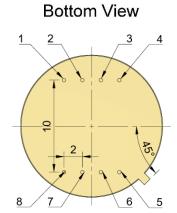


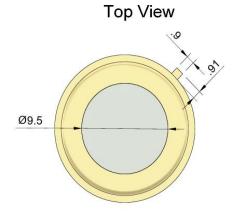


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#### **Mechanical Dimensions 3-Stage TEC Cooling (mm)**



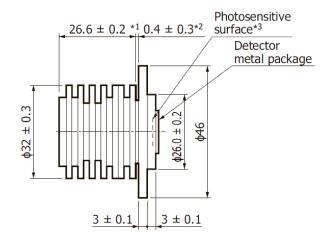


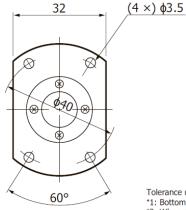


### **Contacts Assignment**

Pin#	Definition		
1	Thermistor		
2	Si Photodiode (+)		
3	Si Photodiode (-)		
4	Thermistor		
5	TEC (-)		
6	MEMS Shutter		
7	MEMS Shutter		
8	TEC (+)		

#### **Heatsink For TEC-Cooled Detector (mm)**





Weight: 50 g approx.

Tolerance unless otherwise noted: ±0.3

- \*1: Bottom surface (reference surface) of detector metal package
- \*2: When detector is installed
- \*3: The position of the photosensitive surface differs according to the detector used.

Refer to the dimensional outline for the detector.

 ${\bf *Product\ dimensions\ may\ change\ without\ notice.\ This\ is\ sometimes\ required\ for\ non-standard\ specifications.}$ 







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### **Ordering Information**

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Prefix	Material Type	ТЕС Туре	Integrated Chopper	Detector Size	Window	AR Coated	Driver
CSAD-	Silicon APD = 8	1 stage -10°C = 1 2 stage -20°C = 2 3 stage -40°C = 3	Non = 1 Yes = 2	1mm = 1 1.7mm x 2.8mm = 2 5mm = 5	Sapphire = 2 Spectral Filter = S Quartz = 1	No = 0 Yes = 1	No = 00 Yes = 11

## **Application Notes**